

SANYO

No. 5082A

LC321664BJ, BM, BT-70/80**1 MEG (65536 words × 16 bits) DRAM
Fast Page Mode, Byte Write**

Overview

The LC321664BJ, BM, BT is a CMOS dynamic RAM operating on a single 5 V power source and having a 65536 words × 16 bits configuration. Equipped with large capacity capabilities, high speed transfer rates and low power dissipation, this series is suited for a wide variety of applications ranging from computer main memory and expansion memory to commercial equipment.

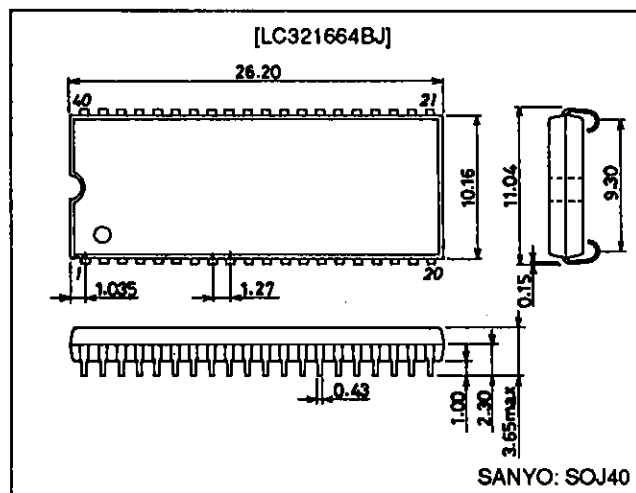
Address input utilizes a multiplexed address bus which permits it to be enclosed in a compact plastic package of 40-pin SOJ. Refresh rates are within 4 ms with 256 row address (A0 to A7) selection and support Row Address Strobe ($\overline{\text{RAS}}$)-only refresh, Column Address Strobe ($\overline{\text{CAS}}$)-before- $\overline{\text{RAS}}$ refresh and hidden refresh settings. There are functions such as fast page mode, read-modify-write and byte write.

Features

- 65536 words × 16 bits configuration.
- Single 5 V ± 10% power supply.
- All input and output (I/O) TTL compatible.
- Supports fast page mode, read-modify-write and byte write.
- Supports output buffer control using early write and Output Enable ($\overline{\text{OE}}$) control.
- 4 ms refresh using 256 refresh cycles.
- Supports $\overline{\text{RAS}}$ -only refresh, $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh and hidden refresh.
- Packages
 - SOJ 40-pin (400 mil) plastic package : LC321664BJ
 - SOP 40-pin (525 mil) plastic package : LC321664BM
 - TSOP 44-pin (400 mil) plastic package : LC321664BT
- $\overline{\text{RAS}}$ access time/column address access time/ $\overline{\text{CAS}}$ access time/cycle time/power dissipation

Package Dimensions

unit: mm

3200-SOJ40

Parameter	LC321664BJ, BM, BT	
	-70	-80
RAS access time	70 ns	80 ns
Column address access time	40 ns	45 ns
CAS access time	25 ns	25 ns
Cycle time	125 ns	135 ns
Power dissipation (max)	During operation	688 mW
	During standby	5.5 mW (CMOS level)/11 mW (TTL level)

SANYO Electric Co., Ltd. Semiconductor Business Headquarters

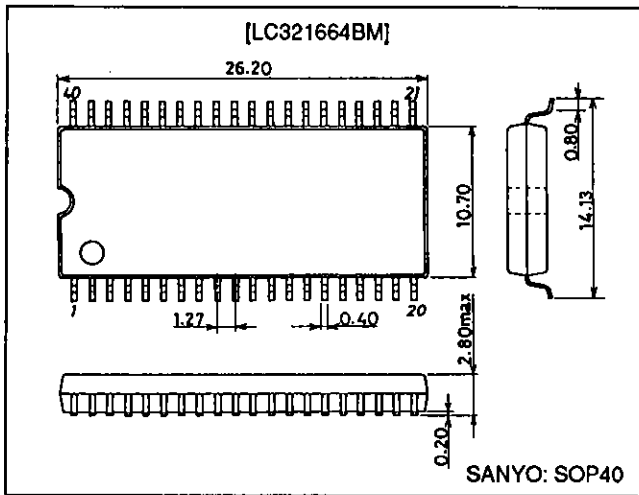
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

LC321664BJ, BM, BT-70/80

Package Dimensions

unit: mm

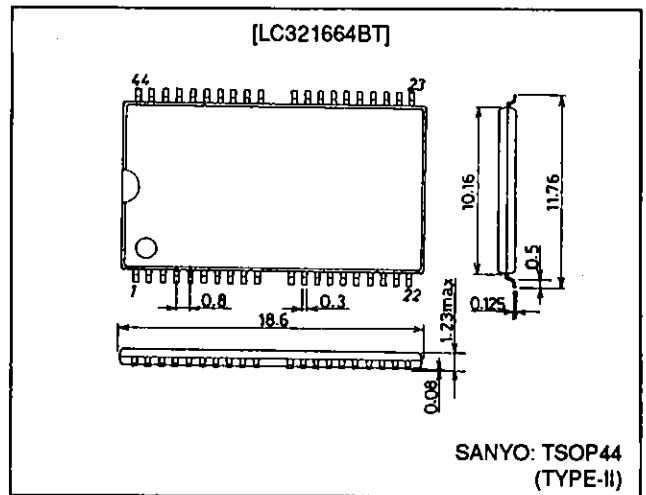
3195-SOP40



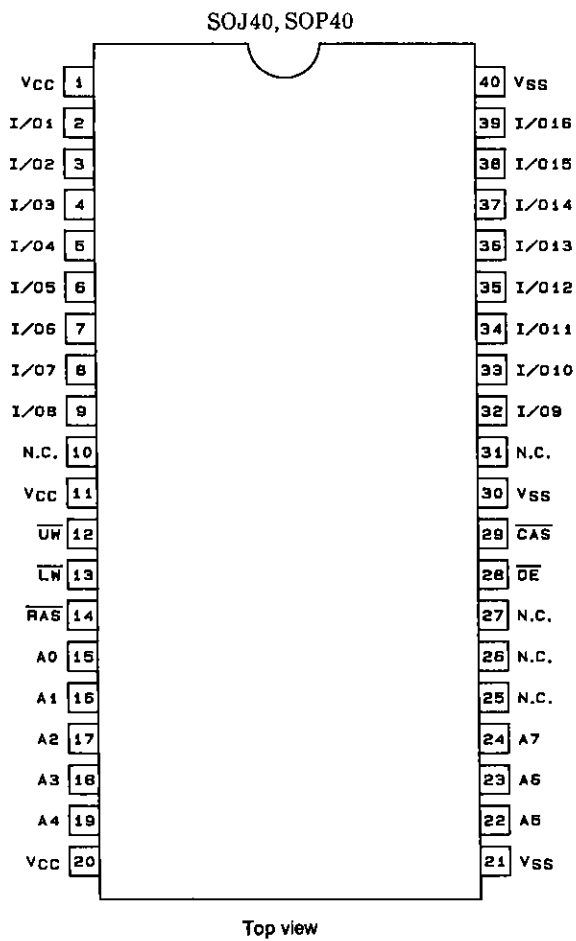
Package Dimensions

unit: mm

3207-TSOP44

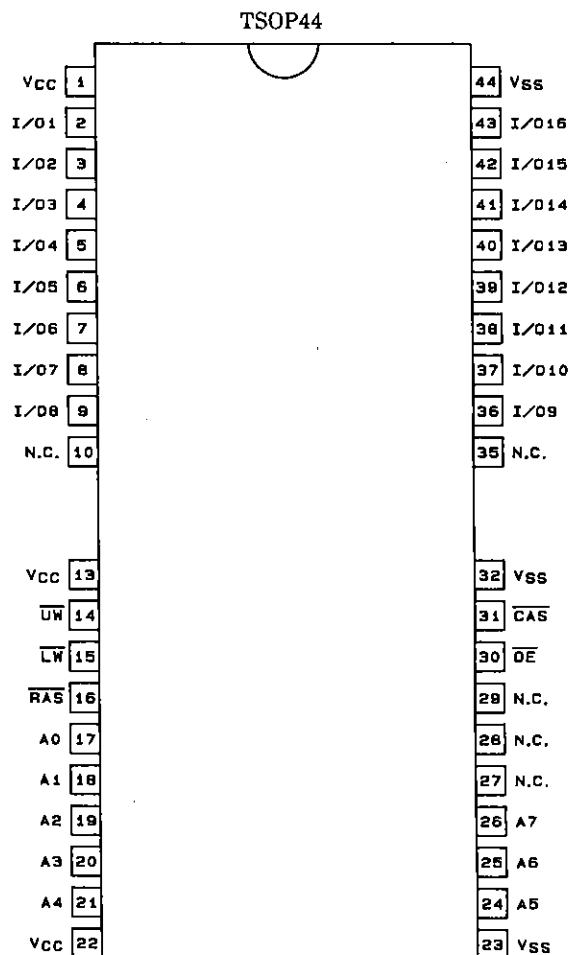


Pin Assignments



Top view

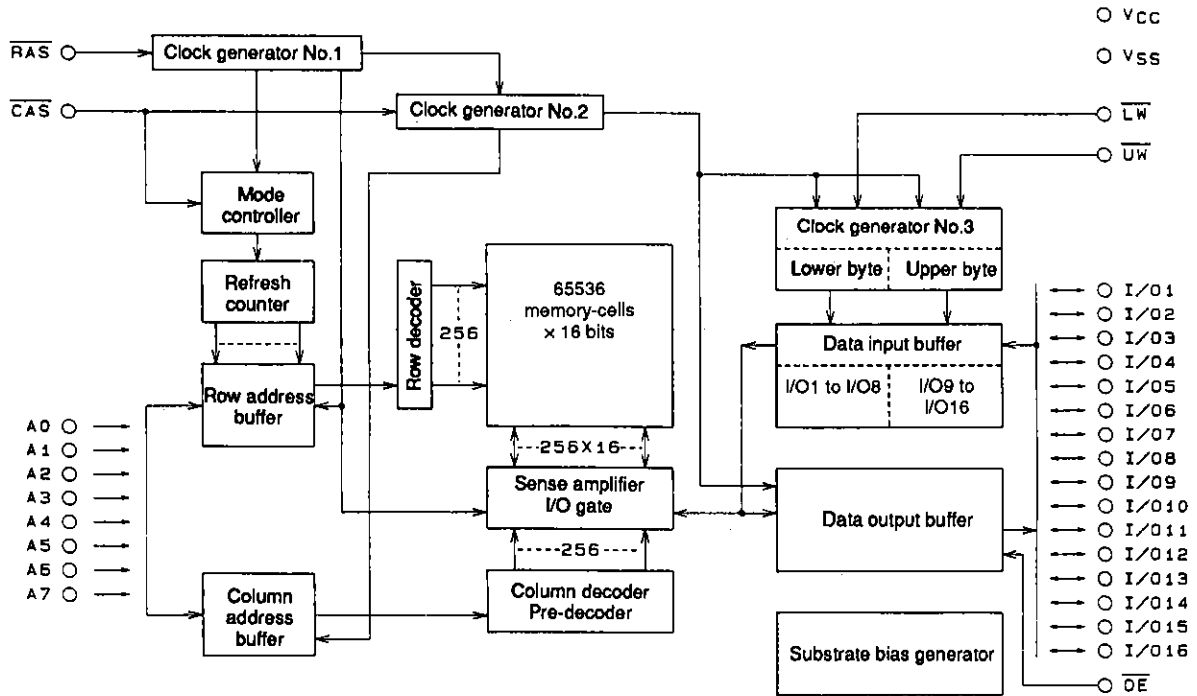
A02123



Top view

A02243

Block Diagram



A02125

Specifications

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit	Note	
Maximum supply voltage	V _{CC} max	-1.0 to +7.0	V	1	
Input voltage	V _{IN}	-1.0 to +7.0	V	1	
Output voltage	V _{OUT}	-1.0 to +7.0	V	1	
Allowable power dissipation	Pd max	LC321664BJ, BM	800	mW	1
		LC321664BT	700		
Output short-circuit current	I _{OUT}	50	mA	1	
Operating temperature range	T _{opr}	0 to +70	°C	1	
Storage temperature range	T _{stg}	-55 to +150	°C	1	

Note: 1. Stresses greater than the above listed maximum values may result in damage to the device.

DC Recommended Operating Ranges at Ta = 0 to +70°C

Parameter	Symbol	min	typ	max	Unit	Note
Power supply voltage	V _{CC}	4.5	5.0	5.5	V	2
Input high level voltage	V _{IH}	2.4		6.5	V	2
Input low level voltage (A0 to A7, RAS, CAS, UW, LW, OE)	V _{IL}	-1.0*		+0.8	V	2
Input low level voltage (I/O1 to I/O16)	V _{IL}	-0.5*		+0.8	V	2

Note: 2. All voltages are referenced to V_{SS}.
A bypass capacitor of about 0.1 μF should be connected between V_{CC} and V_{SS} of the device.
*: -2.0 V when pulse width is less than 20 ns.

LC321664BJ, BM, BT-70/80

DC Electrical Characteristics at Ta = 0 to +70°C, VCC = 5 V ± 10%

Parameter	Symbol	Conditions	LC321664BJ, BM, BT				Unit	Note
			-70		-80			
			min	max	min	max		
Operating current (Average current during operation)	I _{CC1}	RAS, CAS, address cycling: t _{RC} = t _{RC} min		125		115	mA	3, 4, 5
Standby current	I _{CC2}	RAS = CAS = V _{IH}		2		2	mA	
RAS-only refresh current	I _{CC3}	RAS cycling, CAS = V _{IH} : t _{RC} = t _{RC} min		125		115	mA	3, 5
Fast page mode current	I _{CC4}	RAS = V _{IL} , CAS, address cycling: t _{PC} = t _{PC} min		80		70	mA	3, 4, 5
Standby current	I _{CC5}	RAS = CAS = V _{CC} - 0.2 V		1		1	mA	
CAS-before-RAS refresh current	I _{CC6}	RAS, CAS cycling: t _{RC} = t _{RC} min		125		115	mA	3
Input leakage current	I _{IL}	0 V ≤ V _{IN} ≤ 6.5 V, pins other than test pin = 0 V	-10	+10	-10	+10	μA	
Output leakage current	I _{OL}	D _{OUT} disable, 0 V ≤ V _{OUT} ≤ 5.5 V	-10	+10	-10	+10	μA	
Output high level voltage	V _{OH}	I _{OUT} = -2.5 mA	2.4		2.4		V	
Output low level voltage	V _{OL}	I _{OUT} = 2.1 mA		0.4		0.4	V	

Note: 3. All current values are measured at minimum cycle rate. Since current flows immoderately, if cycle time is longer than shown here, current value becomes smaller.

4. I_{CC1} and I_{CC4} are dependent on output loads. Maximum values for I_{CC1} and I_{CC4} represent values with output open.

5. Address change is less than or equal to one time during RAS = V_{IL}. Concerning I_{CC4}, it is less than or equal to one time during 1 cycle (t_{PC}).

AC Electrical Characteristics at Ta = 0 to +70°C, VCC = 5 V ± 10% (Notes 6, 7 and 8)

Parameter	Symbol	LC321664BJ, BM, BT				Unit	Note
		-70		-80			
		min	max	min	max		
Random read, write cycle time	t _{RC}	125		135		ns	
Read-write/read-modify-write cycle time	t _{RWC}	170		180		ns	
Fast page mode cycle time	t _{PC}	50		55		ns	
Fast page mode read-write/read-modify-write cycle time	t _{PRWC}	95		100		ns	
RAS access time	t _{RAC}		70		80	ns	9, 14, 15
CAS access time	t _{CAC}		25		25	ns	9, 14
Column address access time	t _{AA}		40		45	ns	9, 15
CAS precharge access time	t _{CPA}		45		50	ns	9
Output low-impedance time from CAS low	t _{CLZ}	0		0		ns	9
Output buffer turn-off delay time	t _{OFF}	0	20	0	20	ns	10
Rise, fall time	t _T	3	50	3	50	ns	
RAS precharge time	t _{RP}	45		45		ns	
RAS pulse width	t _{RAS}	70	10000	80	10000	ns	
RAS pulse width for fast page mode only	t _{RASP}	70	100000	80	100000	ns	
RAS hold time	t _{RSH}	25		25		ns	
CAS hold time	t _{CSH}	70		80		ns	
CAS pulse width	t _{CAS}	25	10000	25	10000	ns	
RAS to CAS delay time	t _{RCD}	20	45	20	55	ns	14
RAS to column address delay time	t _{RAD}	15	30	15	35	ns	15
CAS to RAS precharge time	t _{CRP}	10		10		ns	
CAS precharge time	t _{CP}	10		10		ns	
Row address setup time	t _{ASR}	0		0		ns	
Row address hold time	t _{RAH}	10		10		ns	
Column address setup time	t _{ASC}	0		0		ns	
Column address hold time	t _{CAH}	15		15		ns	
Column address hold time referenced to RAS	t _{AR}	50		55		ns	
Column address to RAS lead time	t _{RAL}	35		40		ns	
Read command setup time	t _{RCS}	0		0		ns	
Read command hold time referenced to CAS	t _{RCH}	0		0		ns	11
Read command hold time referenced to RAS	t _{RRH}	0		0		ns	11
Write command hold time	t _{WCH}	15		15		ns	
Write command hold time referenced to RAS	t _{WCR}	50		55		ns	

Continued on next page.

LC321664BJ, BM, BT-70/80

Continued from preceding page.

Parameter	Symbol	LC321664BJ, BM, BT				Unit	Note
		-70		-80			
		min	max	min	max		
Write command pulse width	t_{WP}	15		15		ns	
Write command to \overline{RAS} lead time	t_{RWL}	20		20		ns	
Write command to \overline{CAS} lead time	t_{CWL}	20		20		ns	
Data input setup time	t_{DS}	0		0		ns	12
Data input hold time	t_{DH}	15		15		ns	12
Data input hold time referenced to \overline{RAS}	t_{DHR}	50		55		ns	
Refresh time	t_{REF}		4		4	ms	
Write command setup time	t_{WCS}	0		0		ns	13
\overline{CAS} to \overline{UW} , \overline{LW} delay time	t_{CWD}	45		45		ns	13
\overline{RAS} to \overline{UW} , \overline{LW} delay time	t_{RWD}	90		100		ns	13
Column address to \overline{UW} , \overline{LW} delay time	t_{AWD}	60		65		ns	13
\overline{CAS} precharge \overline{UW} , \overline{LW} delay time for fast page mode cycle only	t_{CPWD}	65		70		ns	13
\overline{CAS} setup time for \overline{CAS} -before- \overline{RAS}	t_{CSR}	10		10		ns	
\overline{CAS} hold time for \overline{CAS} -before- \overline{RAS}	t_{CHR}	10		10		ns	
\overline{RAS} precharge \overline{CAS} active time	t_{RPC}	10		10		ns	
\overline{CAS} precharge time for \overline{CAS} -before- \overline{RAS} counter test	t_{CPT}	40		40		ns	
\overline{RAS} hold time referenced to \overline{OE}	t_{ROH}	15		15		ns	
\overline{OE} access time	t_{OEA}		25		25	ns	9
\overline{OE} delay time	t_{OED}	15		15		ns	
\overline{OE} output buffer turn-off delay time	t_{OEZ}	0	15	0	15	ns	10
\overline{OE} command hold time	t_{OEH}	20		20		ns	
Data input to \overline{CAS} delay time	t_{DZC}	0		0		ns	16
Data input to \overline{OE} delay time	t_{DZO}	0		0		ns	16
Masked write setup time	t_{MCS}	0		0		ns	
Masked write hold time referenced to \overline{RAS}	t_{MRH}	0		0		ns	
Masked write hold time referenced to \overline{CAS}	t_{MCH}	0		0		ns	

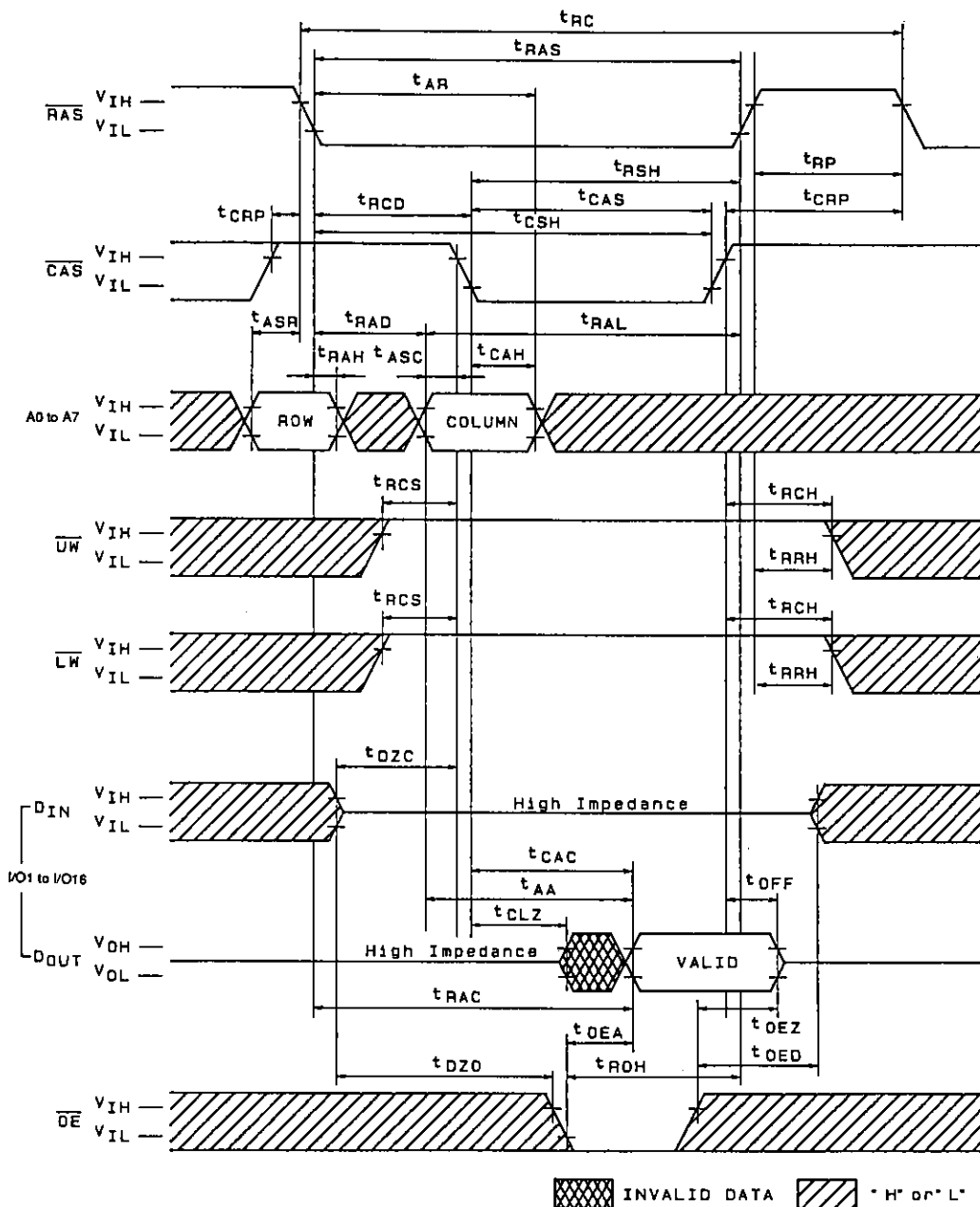
Input/Output Capacitance at $T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{CC} = 5\text{ V} \pm 10\%$

Parameter	Symbol	min	max	Unit	Note
Input capacitance (A0 to A7, \overline{RAS} , \overline{CAS} , \overline{UW} , \overline{LW} , \overline{OE})	C_{IN}		7	pF	
Input/Output capacitance (I/O1 to I/O16)	C_{IO}		7	pF	

- Note:
- An initial pause of 200 μs is required after power-up followed by eight \overline{RAS} -only refresh cycles before proper device operation is achieved. In case of using refresh counter, a minimum of eight \overline{CAS} -before- \overline{RAS} refresh cycles instead of eight \overline{RAS} -only refresh cycles are required.
 - Measured at $t_T = 5\text{ ns}$.
 - When measuring input signal timing, V_{IH} (min) and V_{IL} (max) are used for reference points. In addition, rise and fall time are defined between V_{IH} and V_{IL} .
 - Measured using an equivalent of 50 pF and one standard TTL loads.
 - t_{OFF} (max) and t_{OEZ} (max) are defined as the time until output voltage can no longer be measured when output switches to a high impedance condition.
 - Operation is guaranteed if either t_{RRH} or t_{RCH} is satisfied.
 - These parameters are measured from the falling edge of \overline{CAS} for an early-write cycle, and from the falling edge of \overline{UW} and \overline{LW} for a read-write/read-modify-write cycle.
 - t_{WCS} , t_{CWD} , t_{RWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters for memory in that they specify the operating mode. If $t_{WCS} \geq t_{WCS}$ (min), the cycle switches to an early-write cycle and output pins switch to high impedance throughout the cycle. If $t_{CWD} \geq t_{CWD}$ (min), $t_{RWD} \geq t_{RWD}$ (min), $t_{AWD} \geq t_{AWD}$ (min) and $t_{CPWD} \geq t_{CPWD}$ (min) for fast page mode cycle only, the cycle switches to a read-write/read-modify-write cycle and data output equal information in the selected cells. If neither of the above timings are satisfied, output pins are in an undefined state.
 - t_{RCD} (max) is not a restrictive operating parameter but instead represents the point at which the access time t_{RAC} (max) is guaranteed. If $t_{RCD} \geq t_{RCD}$ (max), access time is determined according to t_{CAC} .
 - t_{RAD} (max) is not a restrictive operating parameter but instead represents the point at which the access time t_{RAC} (max) is guaranteed. If $t_{RAD} \geq t_{RAD}$ (max), access time is determined according to t_{AA} .
 - Operation is guaranteed if either t_{DZC} or t_{DZO} is satisfied.

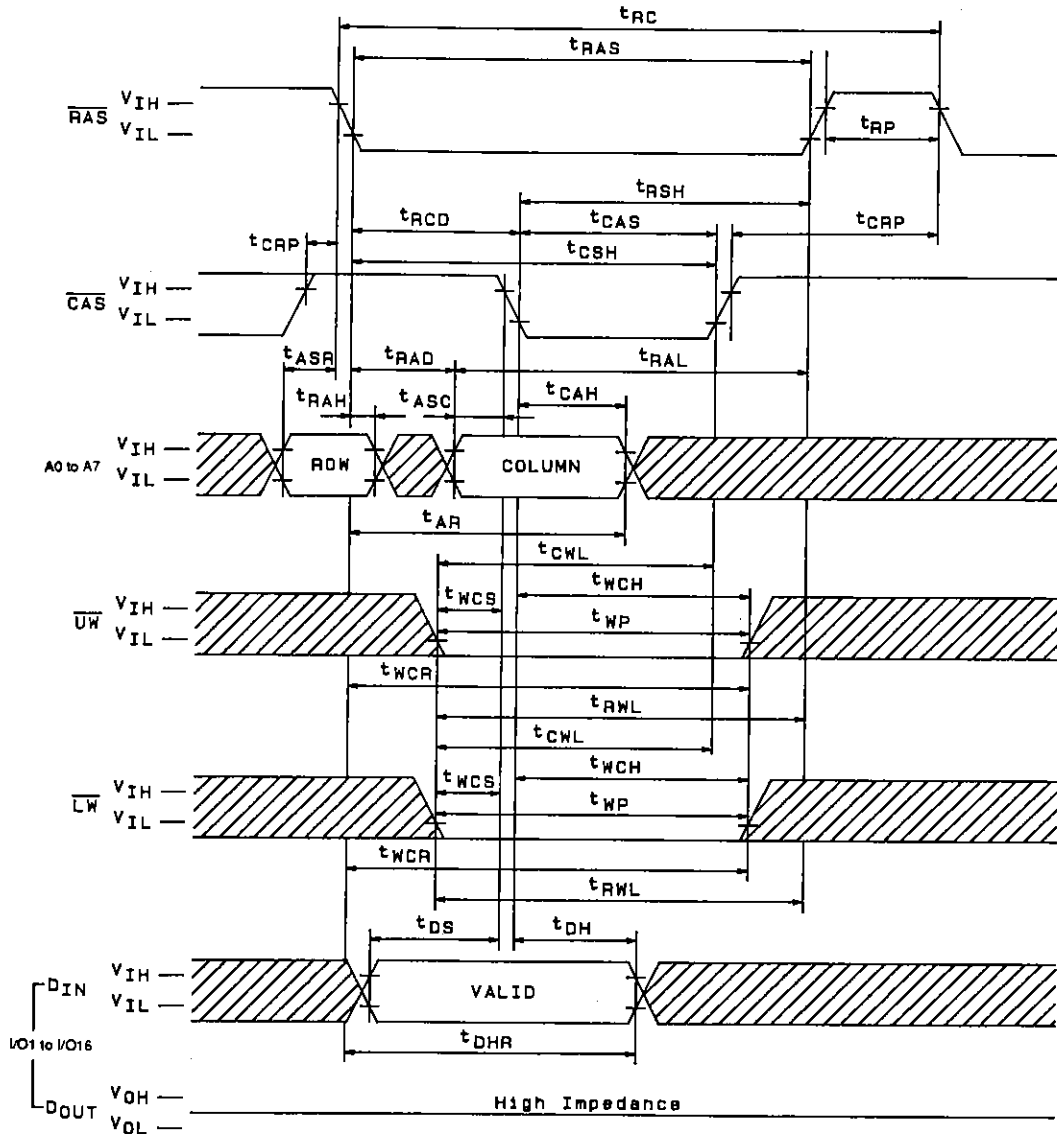
Timing Chart

Read Cycle



A02139

Early Write Cycle

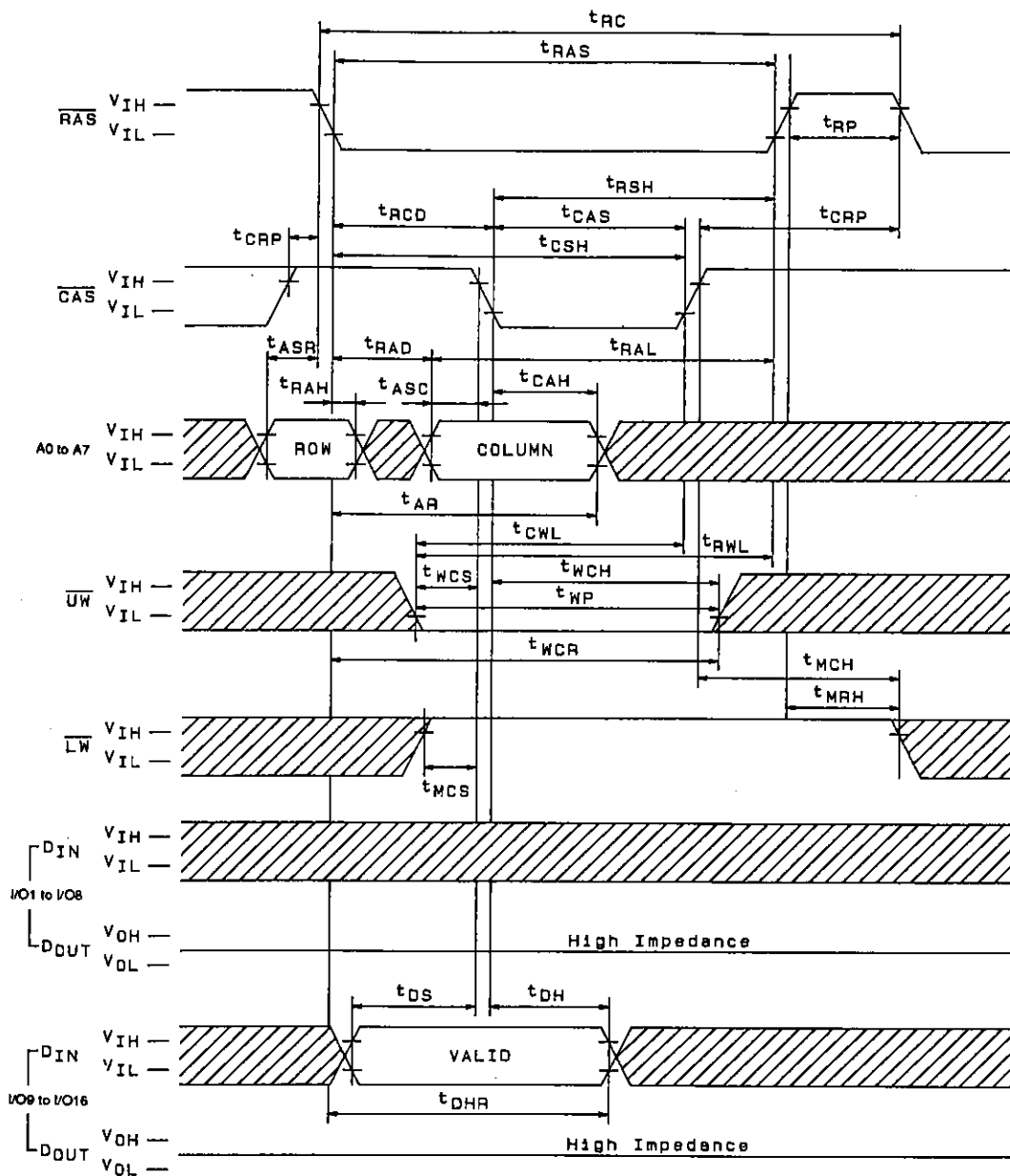


* H* or L*

\overline{OE} : * H* or L*

A02140

Upper Byte Early Write Cycle

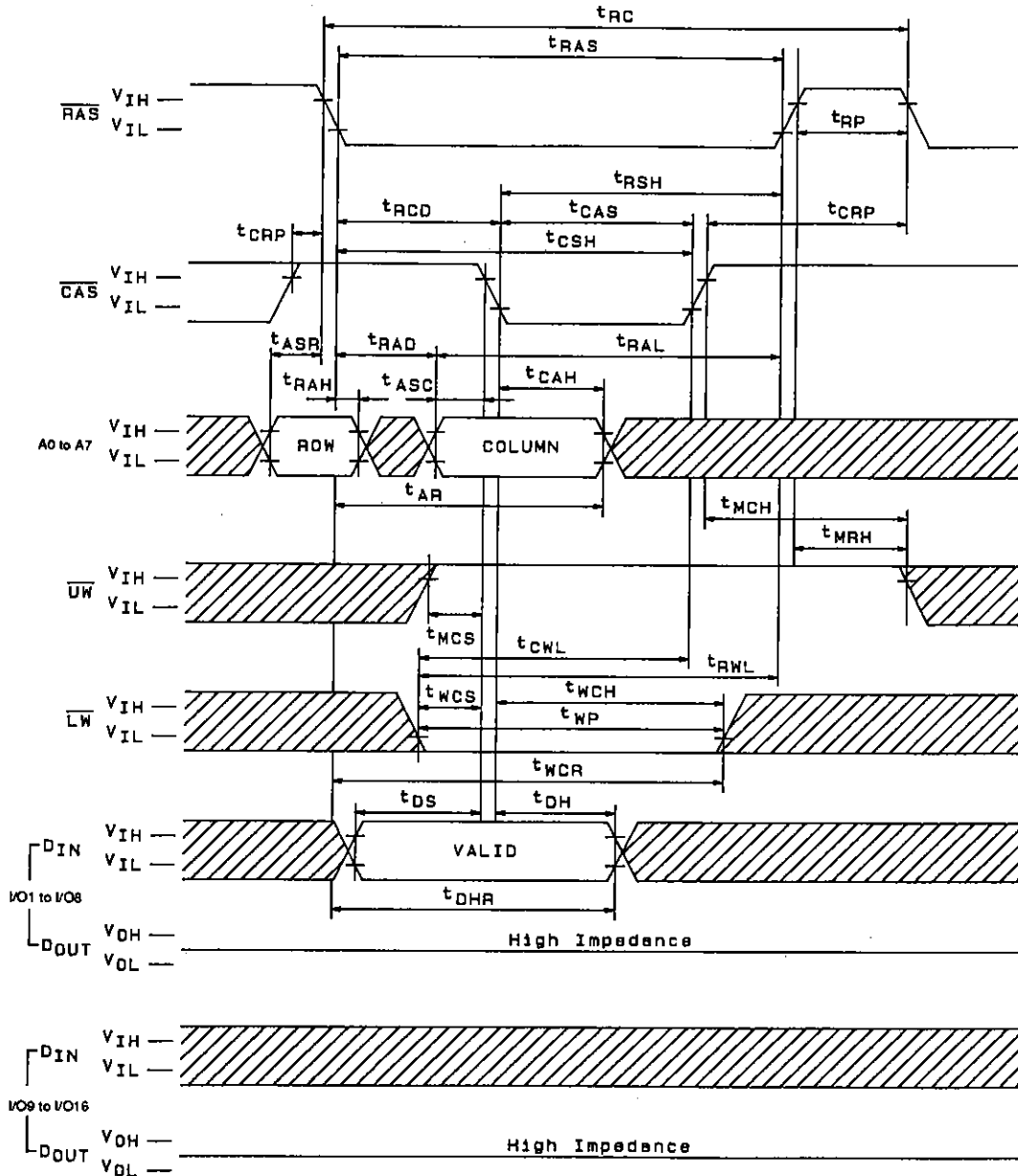


▨ "H" or "L"

\overline{OE} : "H" or "L"

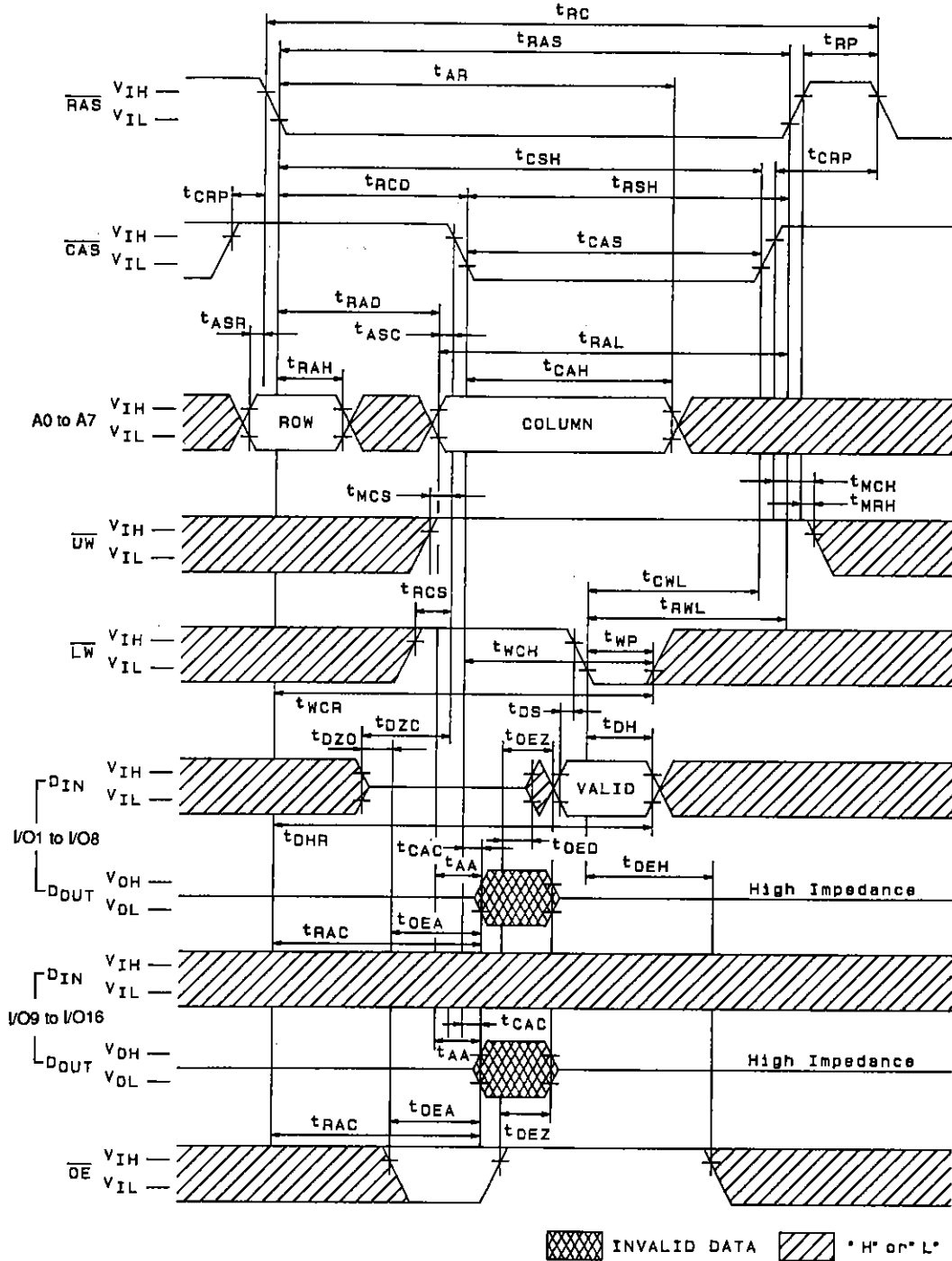
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Lower Byte Early Write Cycle



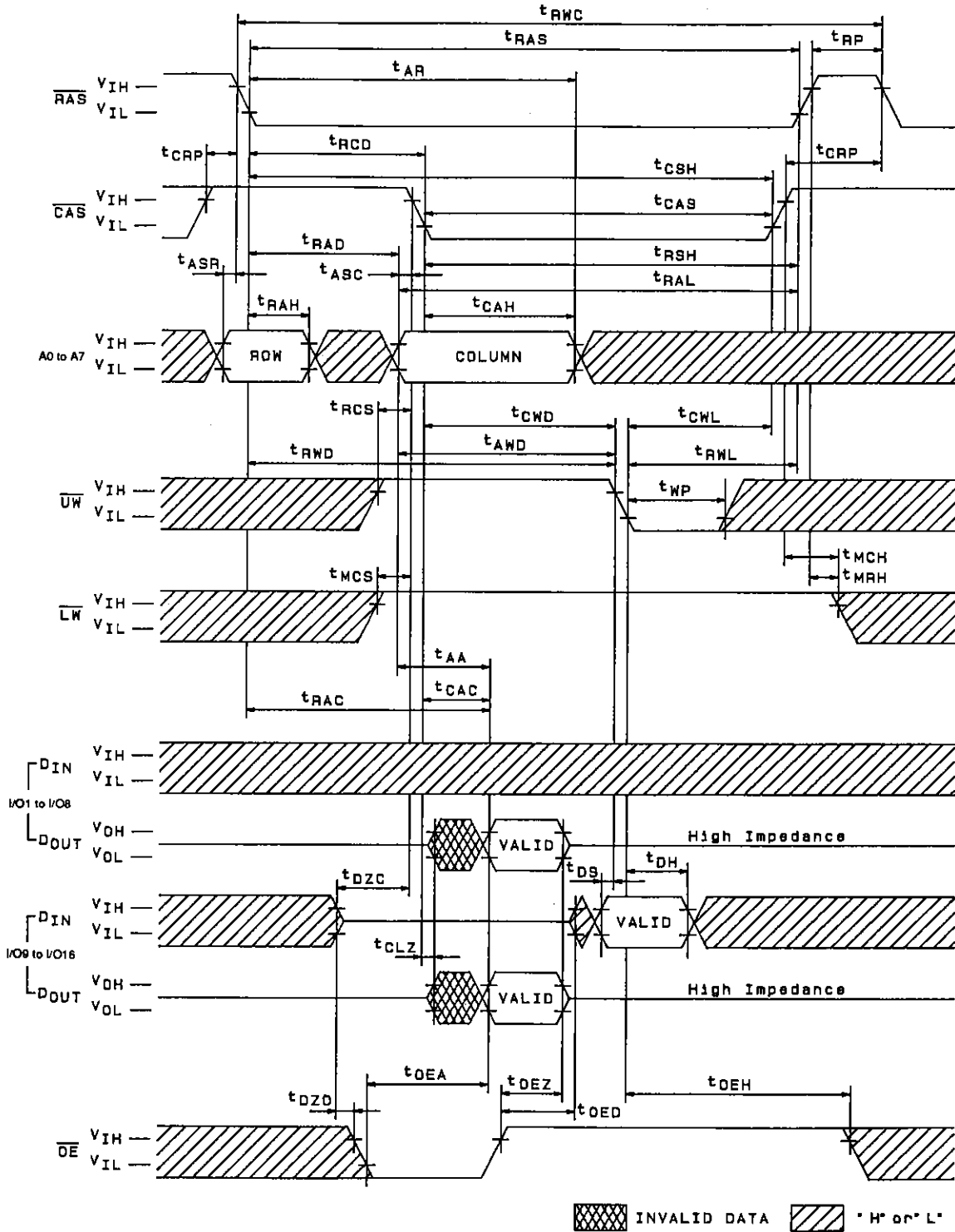
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Lower Byte Write Cycle (\overline{OE} Control)



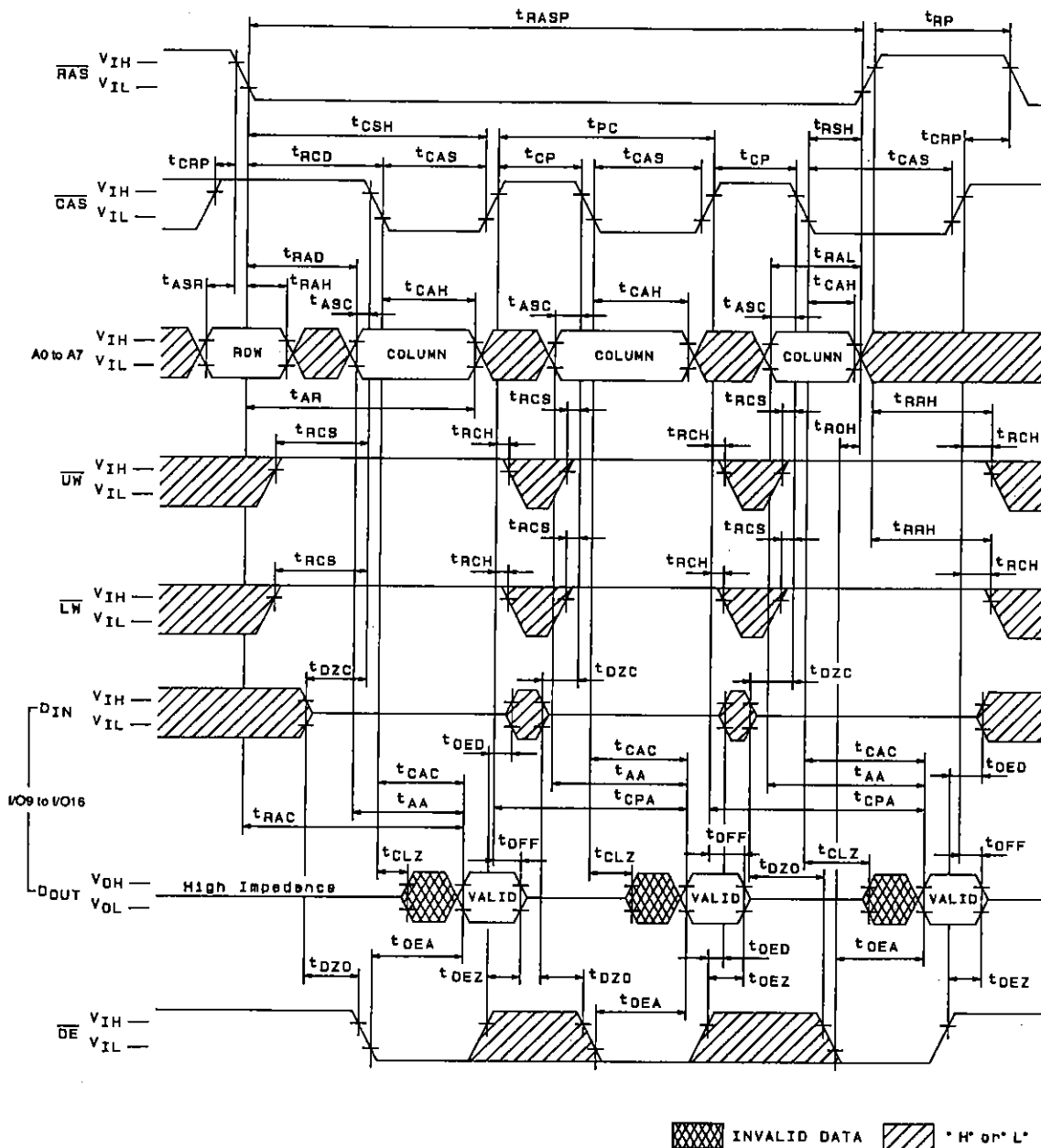
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Read-Modify Upper Byte Write Cycle



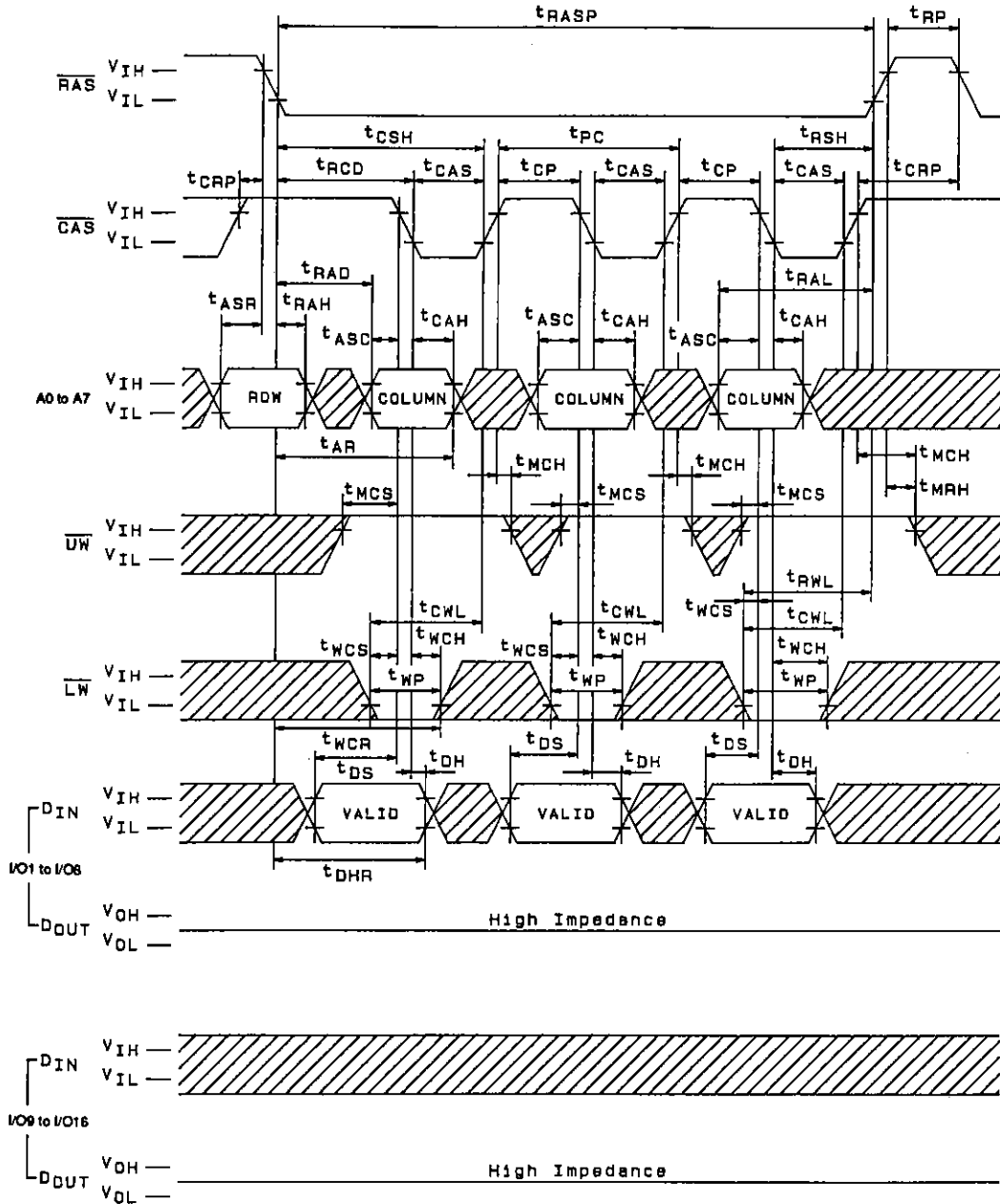
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

Fast Page Mode Read Cycle



A02149

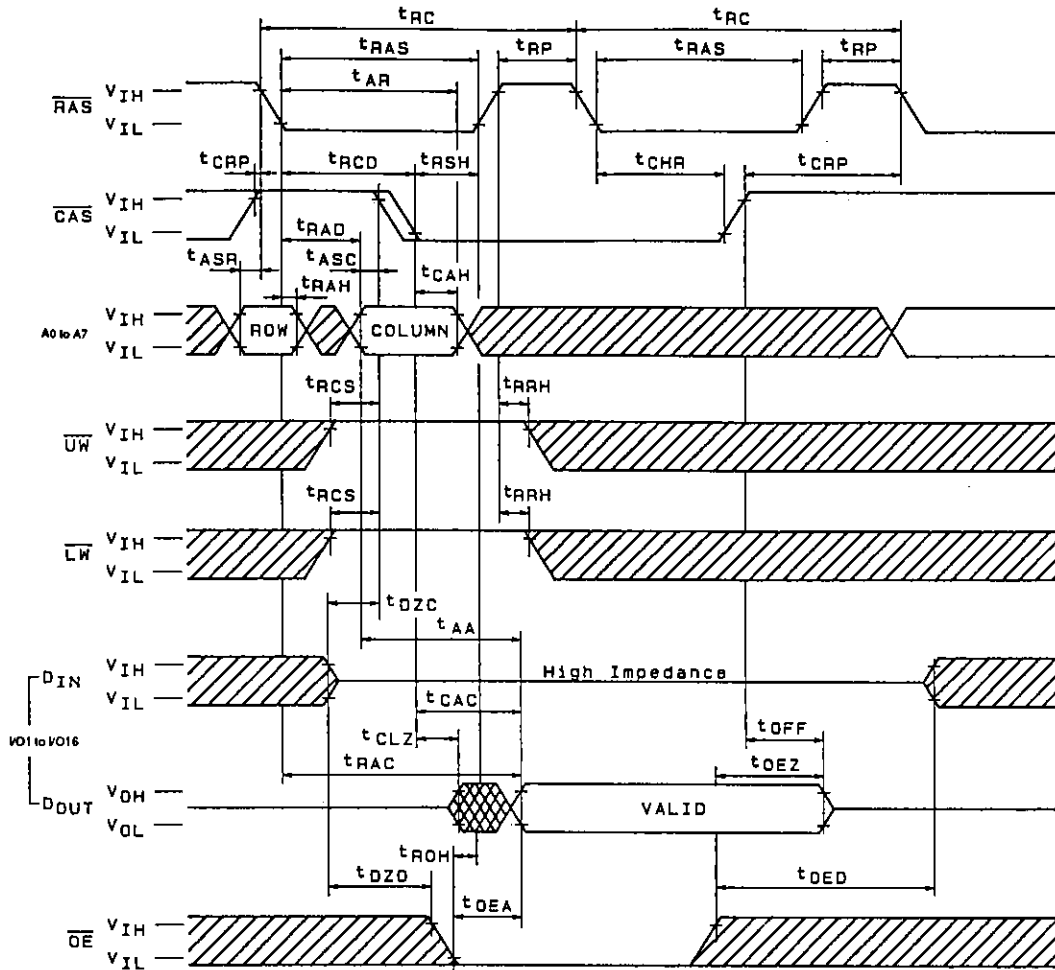
Fast Page Mode Lower Byte Early Write Cycle



 H or L
 OE, H or L

A02162

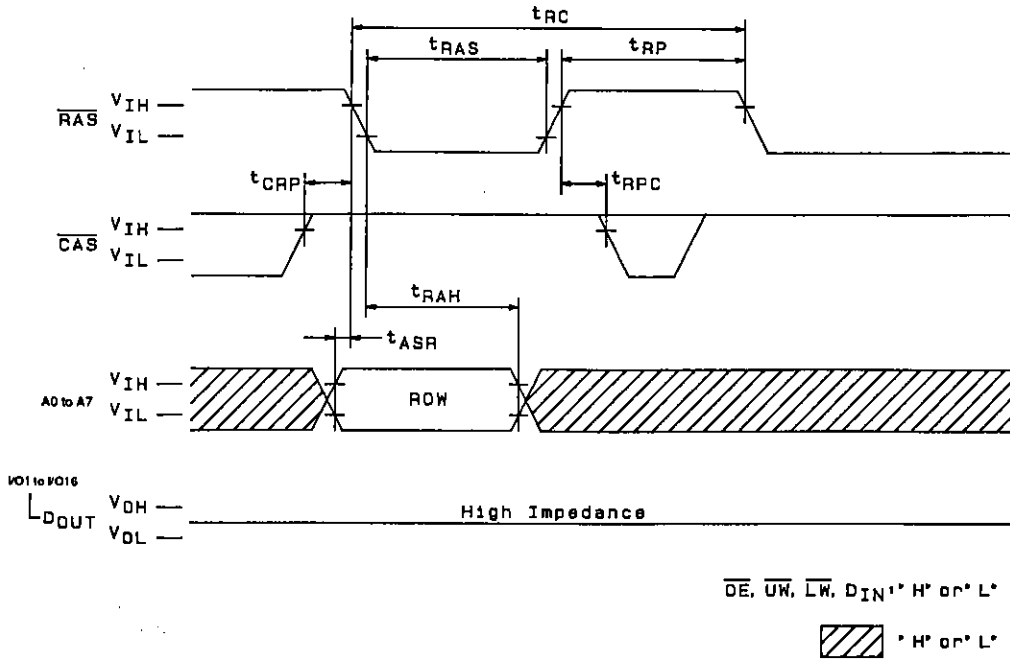
Hidden Refresh Cycle



INVALID DATA "H" or "L"

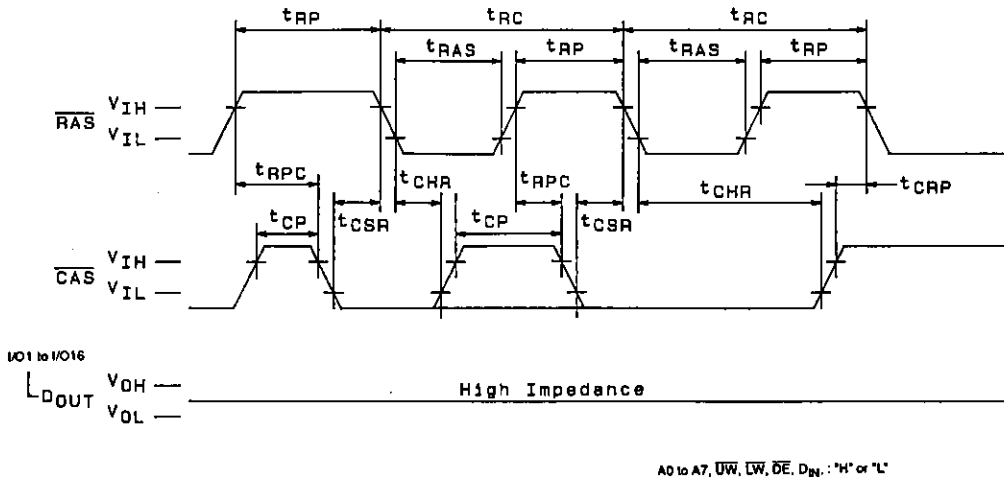
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RAS-Only Refresh Cycle



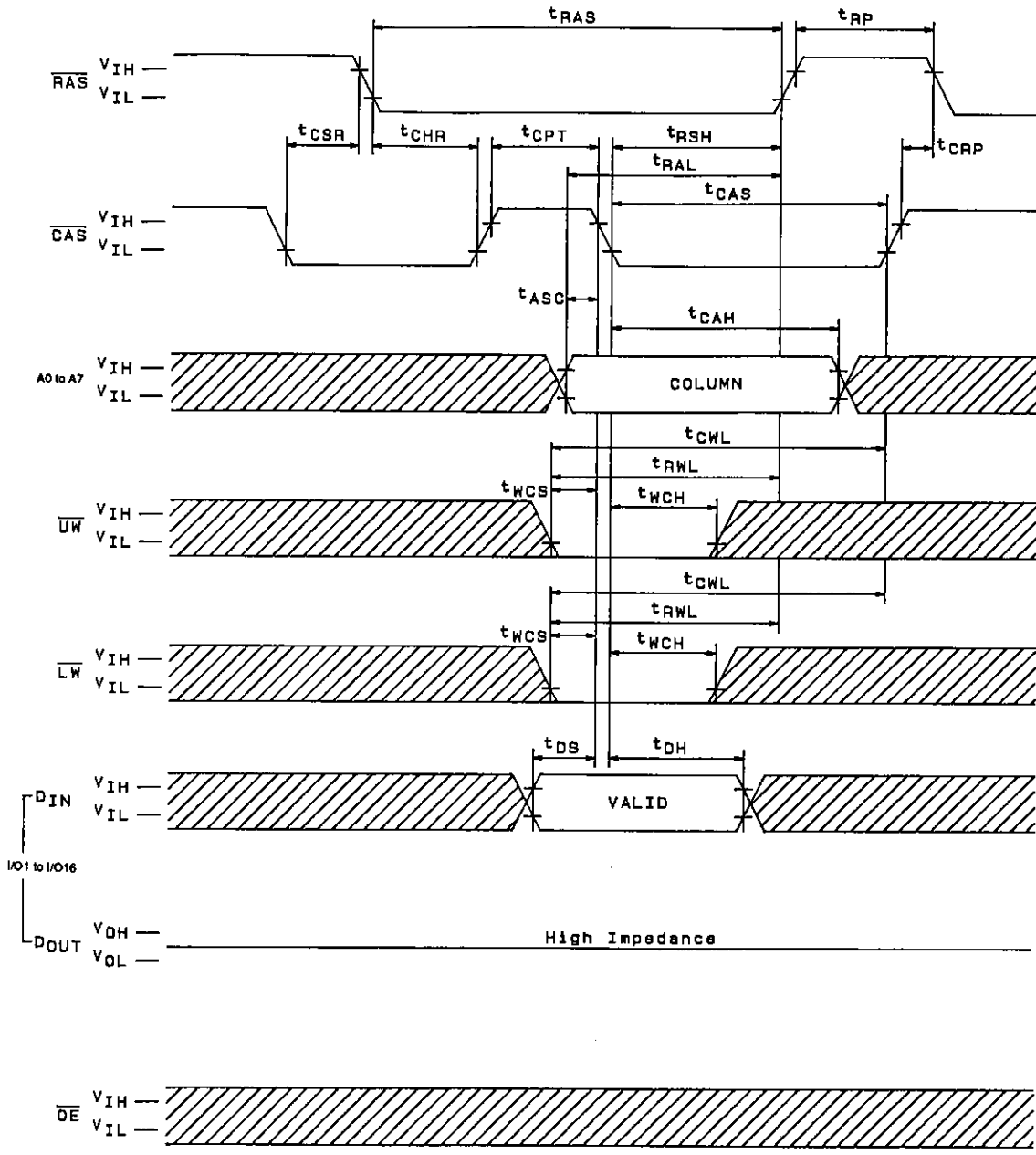
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CAS-Before-RAS Refresh Cycle



A02158

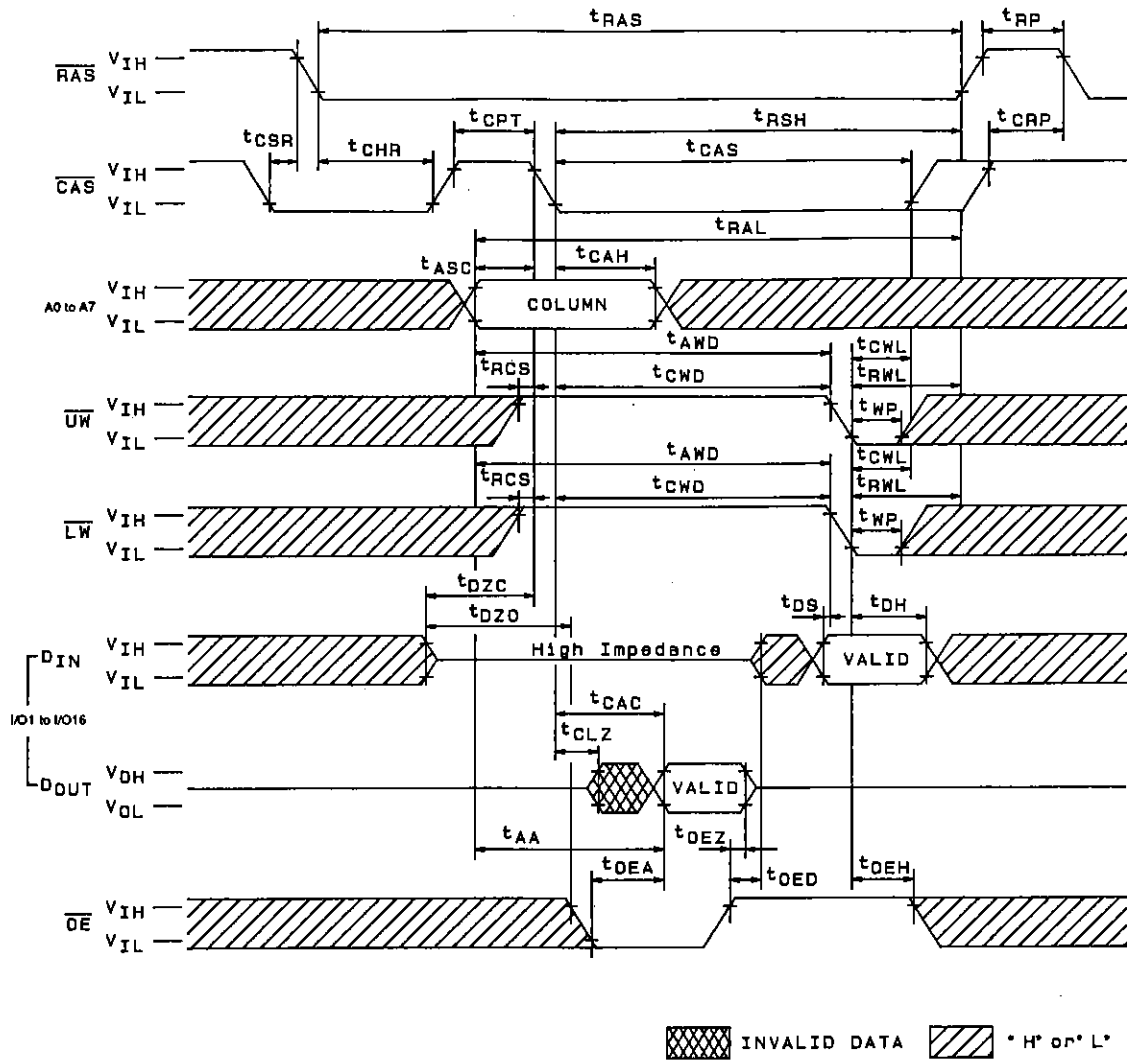
CAS-Before-RAS Refresh Counter Test Cycle (Write)



▨ "H" or "L"

A02180

CAS-Before-RAS Refresh Counter Test Cycle (Read-Modify-Write)



A021B1

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